



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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GROUP 1100

Patent Application of: Sang Young Kim et al.

Application Serial #: 08/327,887

Filed : October 24, 1994

Examiner: B. Everhart

Docket : 9983.3US01

Group Art Unit: 1109

Title : METHOD FOR FILLING CONTACT HOLES WITH METAL BY TWO-STEP DEPOSITION

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Kindly amend the above-identified patent application as follows:

IN THE SPECIFICATION

On page 1, line 6, after "fabricate", kindly replace "high-integrated" with --a highly-integrated--.

On page 5, line 18, after "following process steps", kindly replace the comma with a period.

On page 5, lines 30-31, kindly replace "Hence, in the case of contact with the upper part of the" with --The--.

On page 6, lines 1-2, after "contact hole 30", kindly replace ", the selective films will overgrow appropriately to prevent the misalignment" with --the selective films are overgrown appropriately to prevent misalignment with a second contact hole to be formed above the first contact hole--.

On page 6, line 8, kindly replace "patten" with --pattern--.

On page 6, line 9, kindly replace "fist" with --first--; and replace "a polysilicon" with --the polysilicon--.

On page 6, line 10, kindly replace "the second" with --a second--; and after "hole 40", insert --over each of the first contact hole and the polysilicon 7--.

#15 5/25/95

D1

D2